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	Application No.	Applicant(s)
Notice of Allowability	10/804,430	KIM ET AL.
	Examiner	Art Unit
	Lan Vinh	1765
The MAILING DATE of this communication appears on the cover sheet with the correspondence address All claims being allowable, PROSECUTION ON THE MERITS IS (OR REMAINS) CLOSED in this application. If not included herewith (or previously mailed), a Notice of Allowance (PTOL-85) or other appropriate communication will be mailed in due course. THIS NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT RIGHTS. This application is subject to withdrawal from issue at the initiative of the Office or upon petition by the applicant. See 37 CFR 1.313 and MPEP 1308. 1. This communication is responsive to Amendment filed on 2/9/2006.		
<u> </u>		
2. The allowed claim(s) is/are <u>1,4-21 and 24-39</u> .		
3.		
Attachment(s) 1. ☐ Notice of References Cited (PTO-892) 2. ☐ Notice of Draftperson's Patent Drawing Review (PTO-948) 3. ☑ Information Disclosure Statements (PTO-1449 or PTO/SB/0 Paper No./Mail Date 21306 4. ☐ Examiner's Comment Regarding Requirement for Deposit of Biological Material	6. ☐ Interview Summary Paper No./Mail Dat 8), 7. ☐ Examiner's Amendr	te .

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Allowable Subject Matter

1. Claims 1, 4-21, 24-39 allowed.

The following is an examiner's statement of reasons for allowance:

Regarding claims 1, 21, the cited prior art of record, taken alone or in combination, fails to disclose or suggest a method for etching a substrate comprises a step/limitation of alternatively etching said substrate with a first etchant and a second etchant, wherein said first etchant has a low selectivity to a first hard mask material of said first hard mask layer, a third hard mask material of said a third hard mask layer, and a first barrier layer material of said first barrier layer, but a high selectivity to a second hard mask material of said second hard mask layer, wherein said alternately etching includes etching partially through said low-k layer and said first barrier layer with said second etchant, in combination with the rest of the limitations of claims 1, 21. The closest cited prior art of Soda et al (US 2003/0190907) discloses a method for manufacturing semiconductor device comprises a step of etching partially through a low-k layer 20 with C4F8 gas /second etchant without etching a first barrier layer 19 (col 3, paragraph 0045; fig. 6A-6B)

Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the issue fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for Allowance."

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Conclusion

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2. Any inquiry concerning this communication or earlier communications from the examiner should be directed to Lan Vinh whose telephone number is 571 272 1471. The examiner can normally be reached on M-F 8:30-5:30 PM.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Nadine Norton can be reached on 571 272 1465. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

March 3, 2006